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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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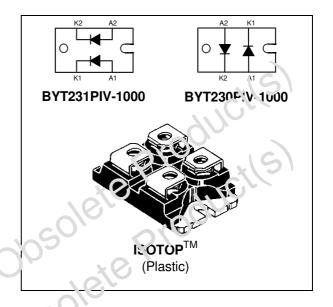
FAST RECOVERY RECTIFIER DIODES

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	2 x 30 A	
V _{RRM}	1000 V	
V _F (max)	1.8 V	
trr (max)	80 ns	

FEATURES AND BENEFITS

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED PACKAGE: ISOTOP Insulation voltage: 2500 V_{RMS} Capacitance = 45 pF Inductance < 5 nH



DESCRIPTION

Dual high voltage rectifier devices are sured for free-wheeling function in convertors and motor control circuits.

Packaged in ISOTOP, they are intended for use in Switch Mode Power Supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit	
V _{BRN} .	Repetitive peak reverse voltage	1000	V	
IFRM	Repetitive peak forward current	700	Α	
I _{F(RMS)}	না As forward current	50	Α	
I:(!\!')	Average forward current	$Tc = 55^{\circ}C$ $\delta = 0.5$	30	А
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	200	Α
T _{stg}	Storage temperature range	- 40 to + 150	°C	
Tj	Maximum operating junction temperature	Maximum operating junction temperature		

TM: ISOTOP is a registered trademark of STMicroelectronics.

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BYT230PIV-1000 / BYT231PIV-1000

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode Total	1.5 0.8	°C/W
R _{th(c)}		Coupling	0.1	

When the diodes 1 and 2 are used simultaneously:

 Δ Tj(diode 1) = P(diode) x R_{th(j-c)} (Per diode) + P(diode 2) x R_{th(c)}

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V _F *	Forward voltage drop	Tj = 25°C	I _F = 30 A			1.9	V
		Tj = 100°C				1.8	51
I _R **	Reverse leakage	Tj = 25°C	V _R = V _{RRM}		1	100	μΑ
	current	Tj = 100°C		- 4	0	5	mA

Pulse test : * tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation: $P = 1.47 \times I_{F(AV)} + 0.010 \ I_{F}^{2}_{(RMS)}$ RECOVERY CHARACTERISTICS (per diads)

Symbol		Test Conditions			Max.	Unit
t _{rr}	Tj = 25℃	$j = 25^{\circ}C$ $I_F = 1A$ $V_{ij} = 30^{\circ}V$ $dI_F/dt = -15A/\mu s$			165	ns
		I _F = 0.5 <i>A</i> I _R = 1A I _{rr} = 0.25A			80	

TURN-OFF SWITCHING CHARACTERISTICS (per diode)

Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
tirm	Maximum reverse	$dI_F/dt = -120 A/\mu s$	$V_{CC} = 200 \text{ V}$			200	ns
L ₀ 0)'	recovery time	$dI_F/dt = -240 A/\mu s$	I _F = 30 A		120		
iF.M	Maximum reverse	dI _F /dt = - 120 A/μs	L _p ≤ 0.05 μH Tj = 100°C			19.5	Α
	recovery current	$dI_F/dt = -240 A/\mu s$	(see fig. 11)		22		
$C = \frac{V_{RP}}{V_{CC}}$	Turn-off overvoltage coefficient	$Tj = 100 ^{\circ}C V_{CC} = 200 V I_{F} = I_{F(AV)}$ $dI_{F}/dt = -30 A/\mu s L_{p} = 5 \mu H$ (see fig. 12)				4.5	/

2/5

Fig. 1: Low frequency power losses versus average current.

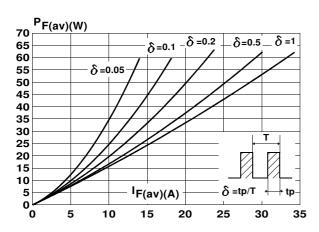


Fig. 3: Non repetitive peak surge current versus overload duration.

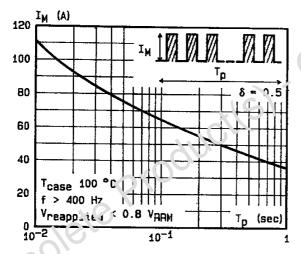


Fig. 5: Voltage drop versus forward current.

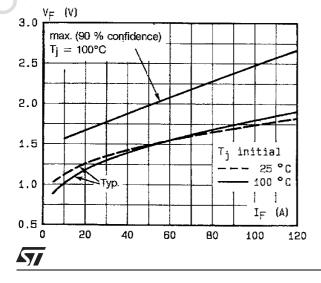


Fig. 2: Peak current versus form factor.

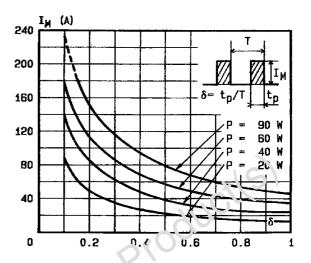


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

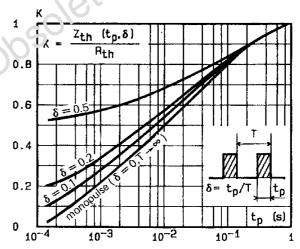


Fig. 6: Recovery charge versus dif/dt.

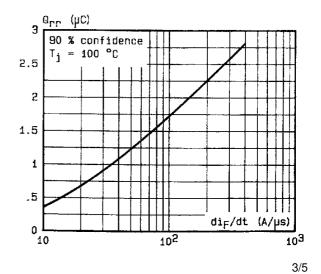


Fig. 7: Recovery time versus dl_F/dt.

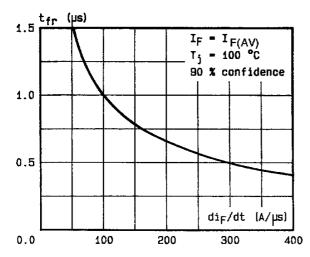


Fig. 9: Peak forward voltage versus dI_F/dt .

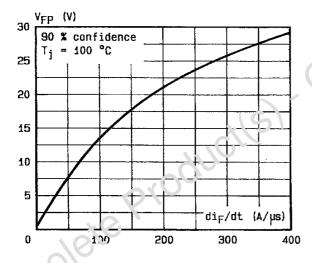


Fig. 11. Furn-off switching characteristics (without serie inductance).

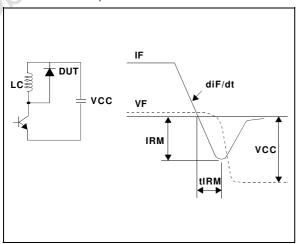


Fig. 8: Peak reverse current versus dl_F/dt.

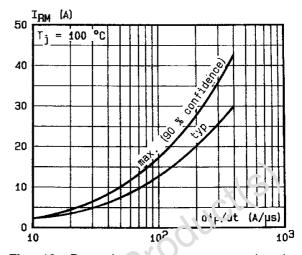


Fig. 10: Dynamic parameters versus junction temperature.

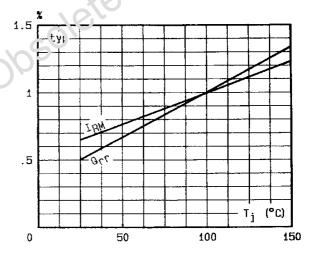
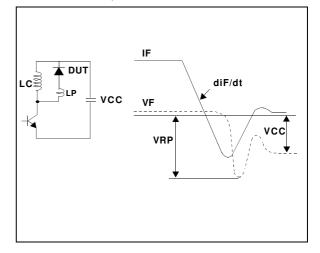
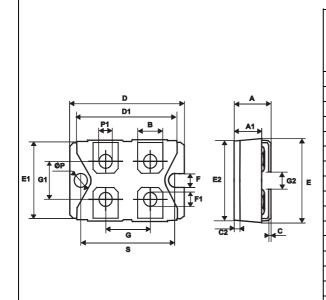


Fig. 12: Turn-off switching characteristics (with serie inductance).



4/5

PACKAGE MECHANICAL DATA ISOTOP



	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
Α	11.80	12.20	0.465	0.480		
A1	8.90	9.10	0.350	0.358		
В	7.8	8.20	0.307	0.323		
С	0.75	0.85	0.030	0.033		
C2	1.95	2.05	0.077	0.081		
D	37.80	38.20	1.488	1.504		
D1	31.50	31.70	1.240	1.2.18		
Е	25.15	25.50	0.990	1.304		
E1	23.85	24.15	0.939	0.951		
E2	24.80 typ.		າ.976	3 typ.		
G	14.90	15.10	0.587	0.594		
G1	12.60	1280	0.496	0.504		
G2	3.50	4.30	0.138	0.169		
F	4.10	4.30	0.161	0.169		
F1	4 (0)	5.00	0.181	0.197		
Р	4.00	4.30	0.157	0.69		
P1	4.00	4.40	0.157	0.173		
722	30.10	30.30	1.185	1.193		

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BYT230PIV-1000	BYT230P:V 1000	ISOTOP	28 g. (without screws)	10	Tube
BYT231PIV-1000	BYT231 L.1.7-1000	ISOTOP	28 g. (without screws)	10	Tube

- Cooling method: by conduction (C)
- Recommend 30 torque value: 1.3 N.m (MAX 1.5 N.m) for the 6 x M4 screws. (2 x M4 screws recommended for mounting the package on the heatsink and the 4 screws given with the screw version). The screws supplied with the package are adapted for mounting on a board (or other types of terminals) with a thickness of 0.6 mm min and 2.2 mm max.
- □ Epcxy meets UL94,V0

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57